

TC74VHC257F, TC74VHC257FN, TC74VHC257FT

QUAD 2 - CHANNEL MULTIPLEXER (3 - STATE)

The TC74VHC257 is an advanced high speed CMOS MULTIPLEXER fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

It is composed of four independent 2 - channel multiplexers with common **SELECT** and **OUTPUTENABLE** (**OE**).

If **OE** is set low, the outputs are held in a high-impedance state. When **SELECT** is set low, "A" data inputs are enabled. Conversely, when **SELECT** is high, "B" data inputs are enabled.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES:

- High Speed..... $t_{pd} = 3.6\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range..... $V_{CC}(\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- Low Noise..... $V_{OLP} = 0.8\text{V}(\text{Max.})$
- Pin and Function Compatible with 74ALS257

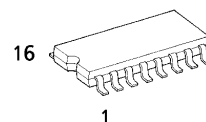
TRUTH TABLE

INPUTS				OUTPUTS
OE	SELECT	A	B	
H	X	X	X	Z
L	L	L	X	L
L	L	H	X	H
L	H	X	L	L
L	H	X	H	H

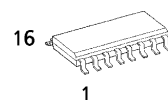
X : Don't Care

Z : High Impedance

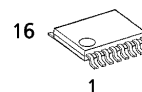
(Note) The JEDEC SOP (FN) is not available in Japan.



F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

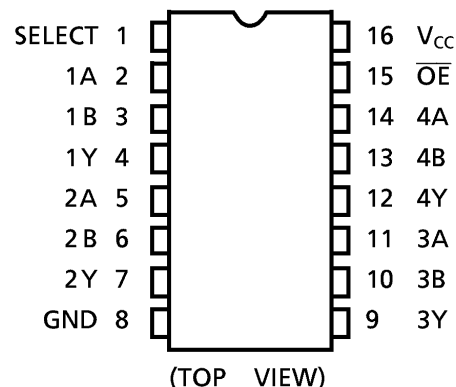


FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)

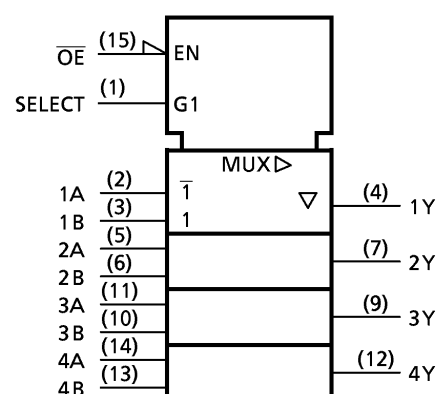


FT (TSSOP16-P-0044-0.65)
Weight : 0.06g (Typ.)

PIN ASSIGNMENT



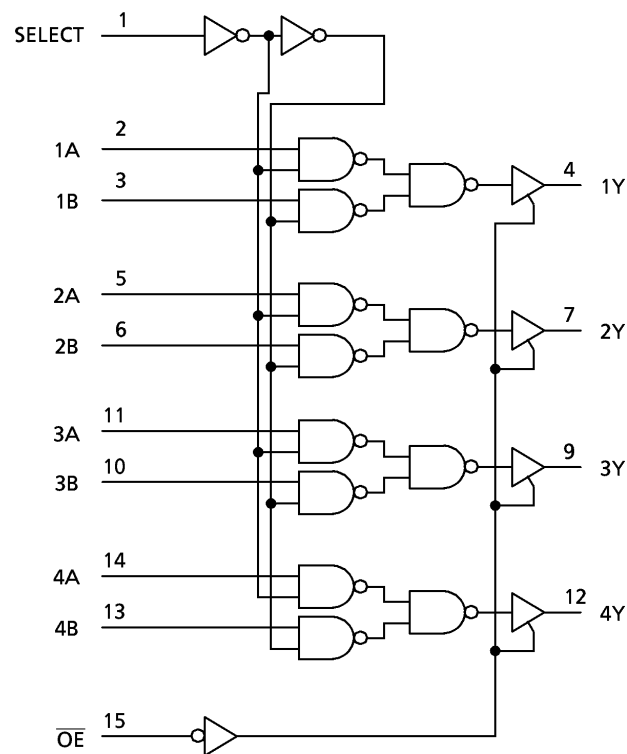
IEC LOGIC



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SYSTEM DIAGRAM



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	$-0.5 \sim 7.0$	V
DC Input Voltage	V_{IN}	$-0.5 \sim 7.0$	V
DC Output Voltage	V_{OUT}	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{stg}	$-65 \sim 150$	$^{\circ}\text{C}$

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	$-40 \sim 85$	$^{\circ}\text{C}$
Input Rise and Fall Time	dt/dv	0~100 ($V_{CC} = 3.3 \pm 0.3\text{V}$) 0~20 ($V_{CC} = 5 \pm 0.5\text{V}$)	ns / V

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 3.0~5.5	1.50 $V_{CC} \times 0.7$	— —	— —	1.50 $V_{CC} \times 0.7$	— —	V
Low - Level Input Voltage	V_{IL}		2.0 3.0~5.5	— —	— —	0.50 $V_{CC} \times 0.3$	— —	0.50 $V_{CC} \times 0.3$	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -50\mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	1.9 2.9 4.4	— — —	V
				3.0 4.5	2.58 3.94	— —	2.48 3.80	— —	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 50\mu\text{A}$	2.0 3.0 4.5	— — —	0.0 0.0 0.0	— — —	0.1 0.1 0.1	V
				3.0 4.5	— —	0.36 0.36	— —	0.44 0.44	
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5	—	—	± 0.25	—	± 2.50	μA
Input Leakage Current	I_{IN}	$V_{IN} = 5.5\text{V or GND}$	0~5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC} \text{ or GND}$	5.5	—	—	4.0	—	40.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION			Ta = 25°C			Ta = − 40~85°C		UNIT
			V _{CC} (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time (A,B-Y)	t _{pLH} t _{pHL}		3.3 ± 0.3	15	—	5.8	9.3	1.0	11.0	ns
				50	—	8.3	12.8	1.0	14.5	
			5.0 ± 0.5	15	—	3.6	5.9	1.0	7.0	
				50	—	5.1	7.9	1.0	9.0	
Propagation Delay Time (SELECT-Y)	t _{pLH} t _{pHL}		3.3 ± 0.3	15	—	7.0	11.0	1.0	13.0	
				50	—	9.5	14.5	1.0	16.5	
			5.0 ± 0.5	15	—	4.0	6.8	1.0	8.0	
				50	—	5.5	8.8	1.0	10.0	
3-State Output Enable Time	t _{pZL} t _{pZH}	RL = 1kΩ	3.3 ± 0.3	15	—	6.7	10.5	1.0	12.5	
				50	—	9.2	14.0	1.0	16.0	
			5.0 ± 0.5	15	—	3.6	6.8	1.0	8.0	
				50	—	5.1	8.8	1.0	10.0	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	RL = 1kΩ	3.3 ± 0.3	50	—	8.6	12.0	1.0	13.5	
			5.0 ± 0.5	50	—	5.7	7.9	1.0	9.0	
Input Capacitance	C _{IN}				—	4	10	—	10	pF
Output Capacitance	C _{OUT}				—	6	—	—	—	
Power Dissipation Capacitance	C _{pd}	Note (1)			—	23	—	—	—	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

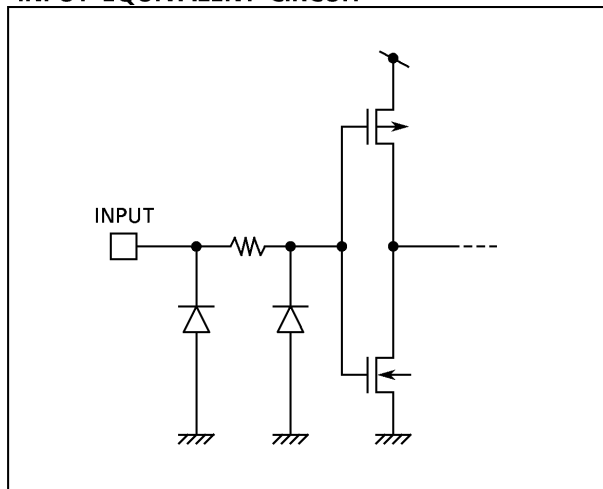
Average operating current can be obtained by the equation :

$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \text{ (per bit)}$$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

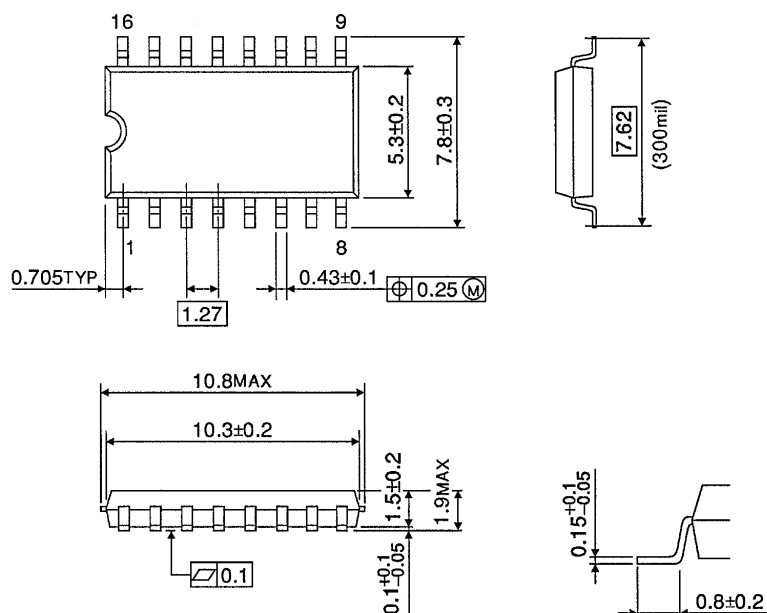
PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C		UNIT
			V _{CC} (V)	TYP.	MAX.	
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	C _L = 50pF	5.0	0.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	C _L = 50pF	5.0	− 0.3	− 0.8	V
Minimum High Level Dynamic Input Voltage	V _{IHD}	C _L = 50pF	5.0	—	3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}	C _L = 50pF	5.0	—	1.5	V

INPUT EQUIVALENT CIRCUIT



SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

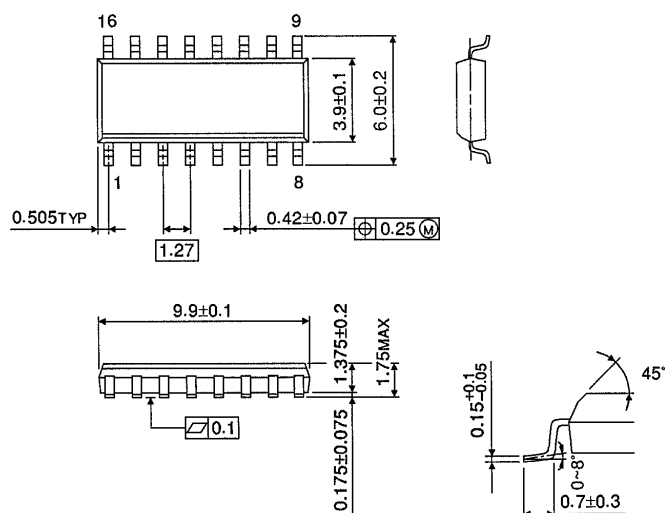


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOP16-P-150-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)

TSSOP 16PIN OUTLINE DRAWING (TSSOP16-P-0044-0.65)

Unit in mm

